Amendments to the Claims:

This listing of claims will replace all prior versions, and listings, of claims in the application.

Listing of Claims:

1. (currently amended) A laser device for generating laser pulses with an optically pumped semiconductor laser, comprising:

a semiconductor laser having an active layer;

a first pump radiation source which is monolithically integrated into the semiconductor laser and configured to optically pump said active layer;

an external resonator; and

at least one mode-locker[[,]].

~~wherein the active layer is optically pumped by the monolithically integrated first pump radiation source.~~

2. (previously presented) The laser device as claimed in claim 1, wherein the semiconductor laser is optically pumped by means of a second pump radiation source arranged externally.

3. (canceled)

4. (previously presented) The laser device as claimed in claim 1, wherein the mode-locker is a passive mode-locker.

5. (previously presented) The laser device as claimed in claim 4, wherein the mode-locker is a saturable absorber.

6. (original) The laser device as claimed in claim 5, wherein the mode-locker is a saturable absorber made of a semiconductor material.

7. (previously presented) The laser device as claimed in claim 1, wherein the mode-locker is monolithically integrated into the semiconductor laser.

8. (previously presented) The laser device as claimed in claim 1, wherein the mode-locker is combined with a resonator mirror.

9. (original) The laser device as claimed in claim 1, wherein the resonator has a device for phase compensation.

10. (original) The laser device as claimed in claim 1, wherein a device for phase compensation is arranged downstream of the resonator.

11. (previously presented) The laser device as claimed in claim 9, wherein the device for phase compensation has at least one of a prism, a grating, a linear or chirped mirror, a lens and an optical fiber.

12. (previously presented) The laser device as claimed in claim 11, wherein the resonator has a chirped folding mirror.

13. (original) The laser device as claimed in claim 1, wherein the resonator has a first resonator branch for generating laser pulses having a fundamental wavelength λ_1 and a second resonator branch for generating laser pulses having a fundamental wavelength λ_2.

14. (previously presented) The laser device as claimed in claim 13, wherein the laser pulses having the fundamental wavelength λ_1 and the laser pulses having the fundamental wavelength λ_2 are coupled to one another in a phase-locked manner.

15. (previously presented) The laser device as claimed in claim 1, wherein the laser pulses have a pulse duration which is less than 100 ps.

16. (original) The laser device as claimed in claim 1, wherein the laser device is a laser oscillator.

17. (original) The laser device as claimed in claim 1, wherein the laser device is a laser amplifier.

18. (original) The laser device as claimed in claim 17, wherein the laser amplifier is a CPA amplifier.

19. (original) The laser device as claimed in claim 1, wherein said mode-locker is arranged in said external resonator.

20. (original) The laser device as claimed in claim 1, wherein a portion of the mode-locker is arranged internally and part is arranged externally of the semiconductor laser.

21. (previously presented) The laser device as claimed in claim 15, wherein the pulse duration is less than 20 ps.

22. (previously presented) The laser device as claimed in claim 21, wherein the pulse duration is less than 1 ps.

23. (previously presented) A laser device for generating laser pulses with an optically pumped semiconductor laser, comprising:

an external resonator; and

at least one mode-locker,

wherein the resonator has a phase compensation element, said phase compensation element compensating for group velocity dispersion.

24. (previously presented) The laser device as claimed in claim 23, wherein the phase element compensation is integrated into the semiconductor laser.

25. (Previously presented) The laser device as claimed in claim 1, wherein the monolithically integrated first pump radiation source is arranged laterally adjacent to the active layer.